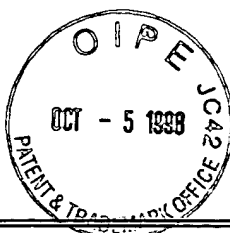


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ATTY. DCKET NO.
 79329

SERIAL NO.
 09/137,084

APPLICANT
 Stumborg, Michael F. et al.

FILING DATE
 08/20/98

GROUP
 2811

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Vh	AA	4,502,209	3/5/85	Eizenberg et al.	29	589	-
	AB	4,965,656	10/23/90	Koubuchi et al.	357	71	-
	AC	5,389,575	2/14/95	Chin et al.	437	190	-
	AD	5,489,548	2/6/96	Niskioka et al.	437	60	-
	AE	5,547,901	8/20/96	Kim et al.	437	187	-
	AF	5,552,341	9/3/96	Lee	437	192	-
	AG	5,554,254	9/10/96	Huang et al.	156	625.1	-
	AH	5,624,874	4/29/97	Lim et al.	438	653	-
	AI	5,637,533	6/10/97	Choi	438	643	-
	AJ	5,668,054	9/16/97	Sun et al.	438	653	-
Vh	AK	5,670,420	9/23/97	Choi	437	189	-

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		

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A circular ink stamp from the Office of the Patent Commissioner. The text "OFFICE OF THE PATENT COMMISSIONER" is arranged in a circle around the date "OCT - 5 1938". The words "PATENT" and "TRADE MARK" are partially visible at the bottom of the stamp.

SERIAL NO.
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20/98	2812

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(Information Disclosure Statement - Section 9 PTO-1449 (Modified) [6-1] page 02 of 03)

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Serial No.

N.C. 79329

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INFORMATION DISCLOSURE STATEMENT
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Applicant
Stumborg, et al.Filing Date
August 20, 1998Group
2811

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
<u>Vu</u>	4,291,327	9/22/81	Tsang	357	52	—
	4,550,331	10/29/85	Milano	357	24	
	4,692,993	9/15/87	Clark et al.	437	53	
	4,847,666	7/11/89	Heremans et al.	357	16	
	5,124,762	6/23/92	Childs et al.	357	16	
	5,435,264	7/25/95	Santiago et al.	117	92	
	5,391,517	2/21/95	Gelatos et al.	437	190	
<u>Vu</u>	5,773,359	6/30/98	Mitchell et al.	438	614	—

FOREIGN PATENT DOCUMENTS

Document	Date	Country	Class	Sub-class	Translation Yes/No
<u>Vu</u> 2-266569	10/31/90	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>Vu</u>	S.M. Sze, "Semiconductor Devices Physics and Technology", 1985, pp. 208-210.
<u>Vu</u>	Truscott, et al., "MBE growth of BaF ₂ /(Ga,In)(As,Sb) Structures", Journal of Crystal Growth, Vol. 81 (1987), pp. 552-556.
<u>Vu</u>	Clemens, et al., "Growth of BaF ₂ and of BaF ₂ /SrF ₂ layers on (001) oriented GaAs", J. Appl. Phys., Vol. 66, No. 4, 15 Aug. 1989, pp. 1680-1685.
<u>Vu</u>	Hung, et al., "Epitaxial growth of alkaline earth fluoride films on HF-treated Si and (NH ₄) ₂ S _x -treated GaAs without <i>in situ</i> cleaning", Appl. Phys. Lett., Vol. 60, No. 2, 13 Jan. 1992, pp. 201-203.

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		Applicant Stumborg, et al.	
		Filing Date August 20, 1998	Group 2811

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U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
V _m	5,690,737	11/25/95	Santiago et al.	117	92	—
V _m	5,695,810	12/9/97	Dubin et al.	427	96	—
V _m	5,824,599	10/20/98	Schacham-Diamond, et al.	437	230	—

FOREIGN PATENT DOCUMENTS

Document	Date	Country	Class	Sub-class	Translation Yes/No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

V _m	Chaudhari, et al., "Calcium Fluoride thin films on GaAs (100) for possible metal-insulator-semiconductor applications", Appl. Phys. Lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.
	Colbow, et al., "Photoemission study of the formation of SrF ₂ /GaAs(100) and BaF ₂ /GaAs(100) interfaces", Physical Review B, Vol. 49, No. 3, 15 Jan. 1994, pp. 1750-1756.
	Chu, et al., "The Role of Barium in the Heteroepitaxial Growth of Insulator and Semiconductors on Silicon", Mat. Res. Symp. Proc., Vol. 334, 1994, pp. 501-506.
	Stumborg, et al., "Determination of growth mechanisms of MBE grown BaF ₂ on Si(100) by target angle dependence of RBS yields", Nucl. Instr. and Methods in Physics Res. B, Vol. 95, 1995, pp. 319-322.
	Stumborg, et al., "Growth and interfacial chemistry of insulating (100) barium fluoride on gallium arsenide", J. Appl. Phys., Vol. 77, No. 6, 15 March 1995, pp. 2739-2744.
	Stumborg, et al., "Surface chemical state populations in the molecular beam epitaxy deposition of BaF ₂ on GaAs by x-ray photoelectron spectroscopy and heavy-ion backscattering spectroscopy", J. Vac. Sci. Technol., Vol. 14, No. 1, Jan./Feb. 1996, pp. 69-79.
V _m	Chu, et al., "Heteroepitaxial deposition of Group IIa fluorides on gallium arsenide", Mat. Sci. and Eng. B, Vol. B47, 1997, pp. 224-234.

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Serial No.

09/137,084

~~not yet assigned~~Applicant
Stumborg, et al.

Filing Date 08/20/98

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Group 2811INFORMATION DISCLOSURE STATEMENT
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U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
✓	4,291,327	9/22/81	Tsang	357	52	—
✓	4,550,331	10/29/85	Milano	357	24	—
✓	4,692,993	9/15/87	Clark et al.	437	53	—
✓	4,847,666	7/11/89	Heremans et al.	357	16	—
✓	5,124,762	6/23/92	Childs et al.	357	16	—
✓	5,435,264	7/25/95	Santiago et al.	117	92	—
✓	5,391,517	2/21/95	Gelatos et al.	437	190	—
✓	5,773,359	6/30/98	Mitchell et al.	438	614	—

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✓	S.M. Sze, "Semiconductor Devices Physics and Technology", 1985, pp. 208-210.
✓	Truscott, et al., "MBE growth of BaF ₂ /(Ga,In)(As,Sb) Structures", Journal of Crystal Growth, Vol. 81 (1987), pp. 552-556.
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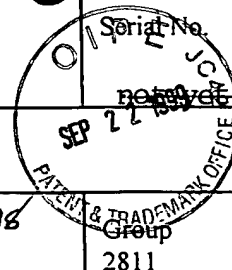
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0a/137; 084

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U.S. PATENT DOCUMENTS

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<u>V_h</u>	5,690,737	11/25/95	Santiago et al.	117	92	—
<u>V_h</u>	5,695,810	12/9/97	Dubin et al.	427	96	—
<u>V_h</u>	5,824,599	10/20/98	Schacham-Diamond, et al.	437	230	—

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<u>V_h</u>	Chaudhari, et al., "Calcium Fluoride thin films on GaAs (100) for possible metal-insulator-semiconductor applications", Appl. Phys. Lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.
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<u>V_h</u>	Chu, et al., "The Role of Barium in the Heteroepitaxial Growth of Insulator and Semiconductors on Silicon", Mat. Res. Symp. Proc., Vol. 334, 1994, pp. 501-506.
<u>V_h</u>	Stumborg, et al., "Determination of growth mechanisms of MBE grown BaF ₂ on Si(100) by target angle dependence of RBS yields", Nucl. Instr. and Methods in Physics Res. B, Vol. 95, 1995, pp. 319-322.
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<u>V_h</u>	Chu, et al., "Heteroepitaxial deposition of Group IIa fluorides on gallium arsenide", Mat. Sci. and Eng. B, Vol. B47, 1997, pp. 224-234.

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Serial No.

09/137,084

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Applicant
STUMBORG ET AL.Filing Date
8/20/98Group
2811

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
<u>h</u>	AA	5,225,031	7/1993	McKee, et al.	156	612	—
<u>h</u>	AB	5,248,633	9/1993	Morar et al.	437	196	—
<u>h</u>	AC	5,378,905	1/1995	Nakamura	257	213	—
<u>h</u>	AD	5,482,003	1/1996	McKee et al.	117	108	—
<u>h</u>	AE	5,593,951	1/1997	Himpel	505	235	—
<u>h</u>	AF	5,753,040	5/1998	Cho	117	106	—

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		Document	Date	Country	Class	Sub-class	Translation Yes/No

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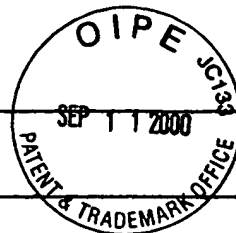
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2811

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
<u>V</u>		5,932,006	8/1999	Santiago et al.	117	92	3/25/96

FOREIGN PATENT DOCUMENTS

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